

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. (canceled)

2. (currently amended) A liquid crystal display device according to Claim ~~[[1;]]~~ 6, wherein the interlayer insulating film ~~[[laid]]~~ between said underneath light-shielding film and metal electrode layer comprises a first interlayer film ~~formed~~ between the underneath light-shielding film and the semiconductor layer as well as a gate insulating film ~~formed~~ between the semiconductor layer and the metal electrode layer~~[[;]]~~ and, on the top of said hill-shaped section, at least a part of said first interlayer film in the direction of the thickness is ~~etched away~~ absent.

3-5. (canceled)

6. (currently amended) ~~A liquid crystal display device according to Claim 4~~ An active matrix type liquid crystal display device having a structure in which a pixel TFT is disposed in a trench in a substrate,

wherein a hill-shaped section encloses at least two sides of the TFT, wherein an underneath light-shielding film is disposed beneath a semiconductor layer of the TFT so as to reach at least a top of said hill-shaped section and a metal electrode

layer formed above the semiconductor layer of the TFT extends to the top of said hill-shaped section,

wherein on the top of said hill-shaped section, a film thickness of an interlayer insulating film between said underneath light-shielding film and metal electrode layer is thinner than in other sections thereof, and

wherein a portion of said semiconductor layer of the TFT constitutes a storage capacitor section and the interlayer film laid between the semiconductor layer and the underneath light-shielding film in said storage capacitor section is made thinner than in the TFT section.

7-21. (canceled)

22. (new) An active matrix liquid crystal display device comprising:

a layer of first insulating material having at least two spaced-apart ridges thereon;

a light shielding film on said first insulating material and extending between and to tops of said at least two ridges;

a layer of second insulating material on said light shielding film, said layer of second insulating material having a first thickness between said at least two ridges and a second thickness less than the first thickness at the tops of said at least two ridges, whereby a light path through said layer of

second insulating material is constricted by the second thickness;

a pixel thin film transistor (TFT) on said layer of second insulating material between said at least two ridges; and

a metal electrode over said TFT and extending between and to the tops of said at least two ridges.

23. (new) The device of claim 22, comprising four of said ridges that enclose said TFT.

24. (new) The device of claim 22, wherein said metal electrode is a gate electrode and further comprising a gate insulating film beneath said gate electrode.